

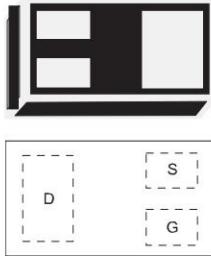
Features

BV_{DSS}	30V
$R_{DS(ON)}$	450mΩ
I_D	800mA

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

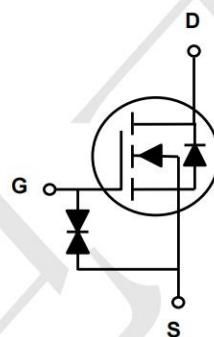
Package and Pin Configuration



DFN1006-3L

Marking:35

Circuit diagram



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous($T_C=25^\circ\text{C}$)	I	800	mA
Drain Current-Pulsed ¹	I_{DM}	2100	mA
Power Dissipation($T_C=25^\circ\text{C}$)	P_D	155	mW
Power Dissipation-Derate Above 25°C		1.25	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	800	°C/W
Storage Temperature Range	T_{STG}	-55 To +150	°C
Operating Junction Temperature Range	T_J	-55 To +150	°C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Reference to 25°C , $I_{\text{D}}=1\text{mA}$	-	-0.03	-	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	$I_{\text{DS}(\text{SS})}$	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{\text{DS}}=24\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 20	μA
On Characteristics						
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=0.5\text{A}$	-	350	450	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=0.5\text{A}$	-	450	650	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.5	0.8	1.2	V
$V_{\text{GS}(\text{th})}$ Temperature Coefficient	$\Delta V_{\text{GS}(\text{th})}$		-	-1.74	-	$\text{mV}/^\circ\text{C}$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=4\text{V}, I_{\text{D}}=0.3\text{A}$	-	1	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q_g	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=0.3\text{A}, V_{\text{GS}}=4.5\text{V}$	-	2.6	5.2	nC
Gate-Source Charge ^{2,3}	Q_{gs}		-	0.9	1.8	
Gate-Drain Charge ^{2,3}	Q_{gd}		-	0.6	1.2	
Turn-On Delay Time ^{2,3}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=15\text{V}, R_{\text{G}}=10\Omega, V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=0.3\text{A}$	-	5.5	11	nS
Rise Time ^{2,3}	t_r		-	4	8	
Turn-Off Delay Time ^{2,3}	$t_{\text{d}(\text{off})}$		-	14.5	29	
Fall Time ^{2,3}	t_f		-	6.5	13	
Input Capacitance	C_{iss}		-	72.9	146	PF
Output Capacitance	C_{oss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	18.3	36.6	
Reverse Transfer Capacitance	C_{rss}		-	7.4	14.8	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_s	$V_G=V_D=0\text{V}, \text{Force Current}$	-	-	400	mA
Pulsed Source Current	I_{SM}		-	-	800	
Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=0.2\text{A}, T_J=25^\circ\text{C}$	-	-	1	V
Reverse Recovery Time	T_{rr}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=0.3\text{A}, d_i/d_t=100\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$	-	13	-	nS
Reverse Recovery Charge	Q_{rr}		-	6	-	nC

Typical Electrical and Thermal Characteristic Curves

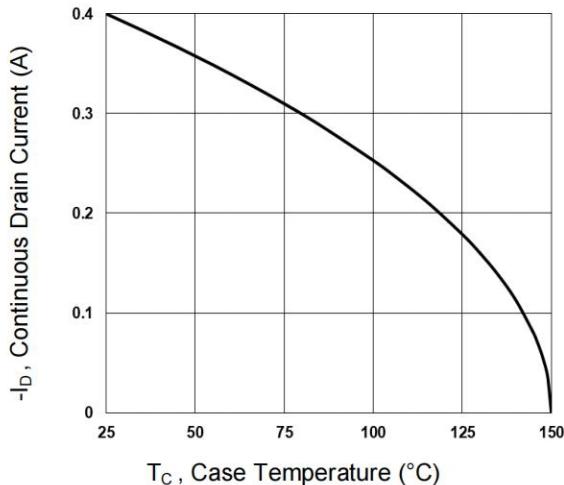


Figure 1. Continuous Drain Current vs. T_C

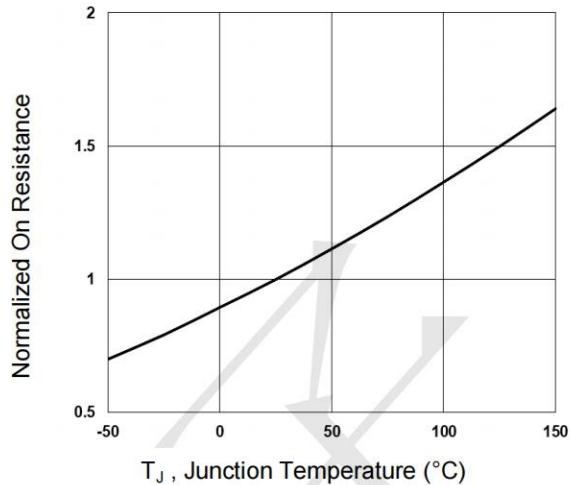


Figure 2. Normalized $R_{DS(on)}$ vs. T_J

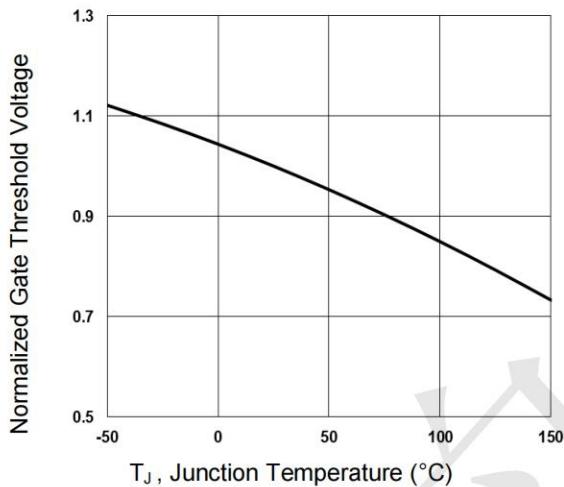


Figure 3. Normalized V_{th} vs. T_J

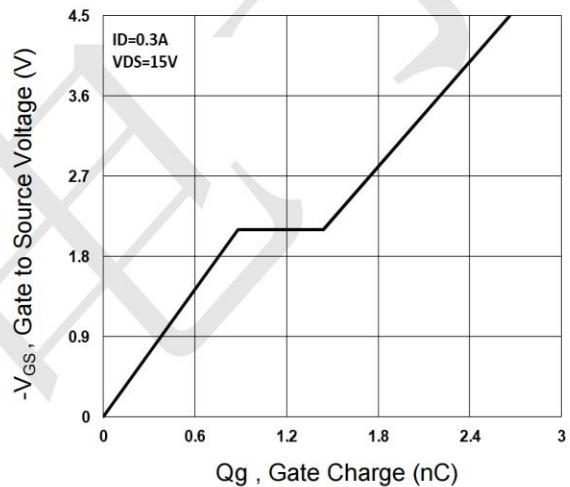


Figure 4. Gate Charge Waveform

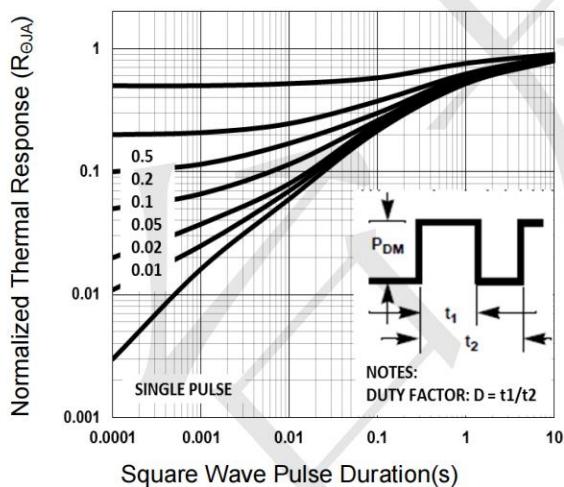


Figure 5. Normalized Transient Response

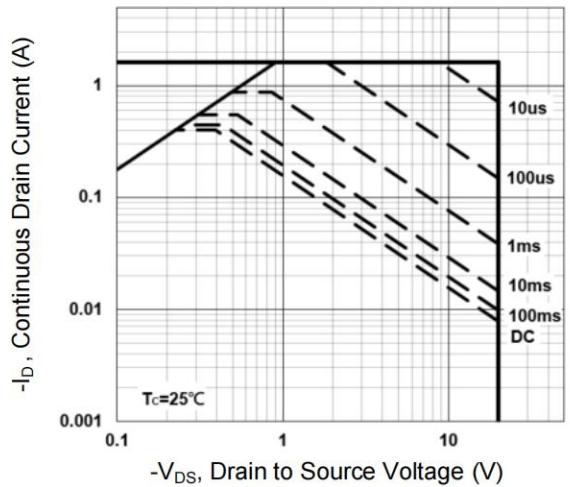


Figure 6. Maximum Safe Operation Area

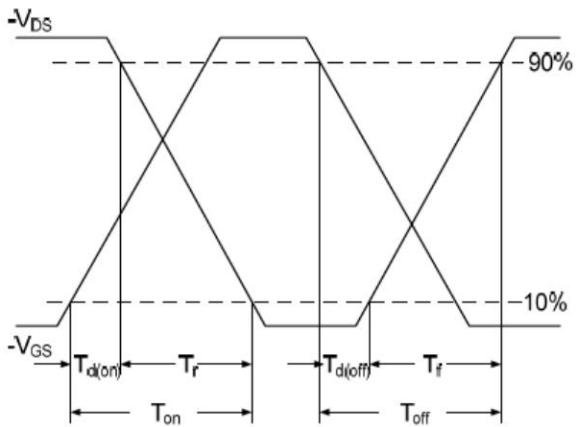


Figure 7. Switching Time Waveform

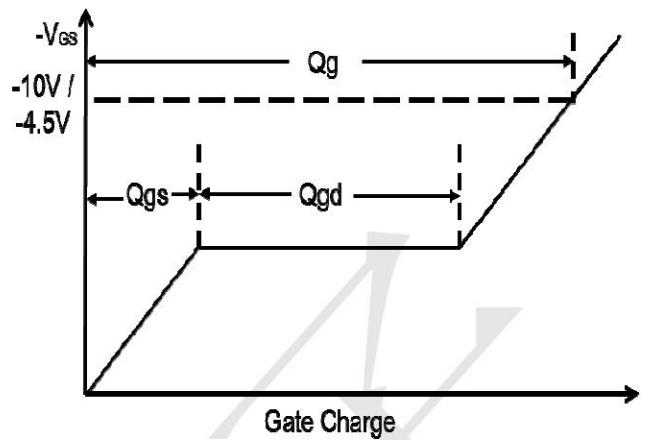
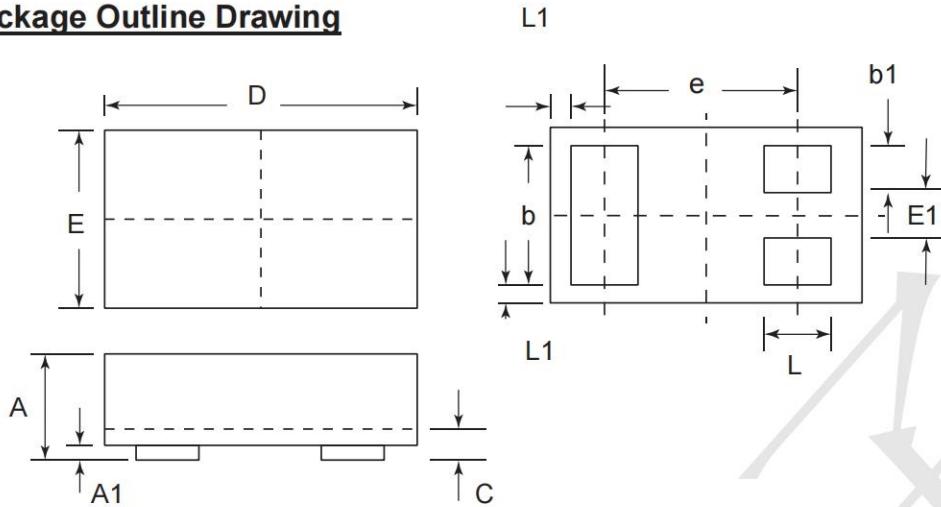


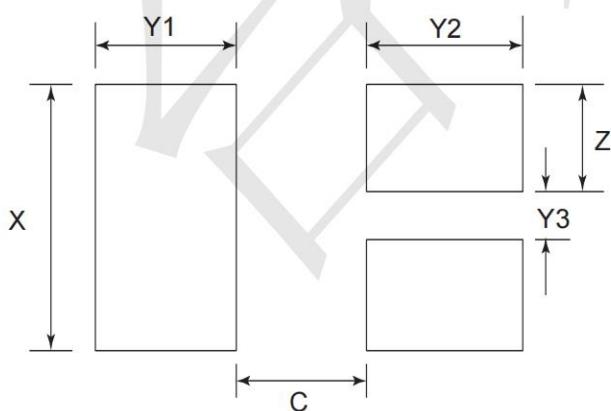
Figure 8. Gate Charge Waveform

DFN1006-3L Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
C	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008